SILICON NPN RF TRANSISTOR

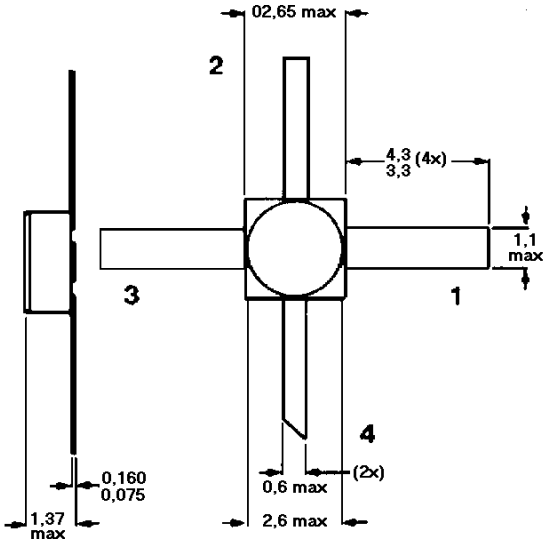
DESCRIPTION:

The **2N6679** is Designed for 4.0 GHz Small Signal Thin and Thick Film RF Amplifier Applications.

MAXIMUM RATINGS

I_C	70 mA
V_{CE}	20 V
P_{DISS}	900 mW @ T_C = 87 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
θ_{JC}	194 ^{O}C/W

PACKAGE STYLE SOT-100



1 = Emitter 2 = Base 3 = Emitter 4 = Collector
(Dimensions are in millimeters)

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 100 µA	30			V
I_{CEO}	V_{CE} = 15 V			500	nA
I_{CBO}	V_{CB} = 15 V			100	nA
h_{FE}	V_{CE} = 15 V I_C = 15 mA	50	100	220	---
C_{ob}	V_{CB} = 10 V f = 1.0 MHz (EMITTER CONNECTED TO GUARD TERMINAL OF BRIDGE)		0.27		pF
G_t	V_{CE} = 15 V I_C = 25 mA f = 4.0 GHz	9.0	10.5		dB
P_{1db}	V_{CE} = 15 V I_C = 25 mA f = 4.0 GHz		18.5		dBm